ECH8651R

N-Channel Power MOSFET 24V, 10A, 14mΩ, Dual ECH8



ON Semiconductor®

http://onsemi.com

Features

- · Low ON-resistance
- · 2.5V drive
- · Common-drain type
- · Protection diode in

- · Built-in gate protection resistor
- · Best suited for LiB charging and discharging switch
- · Halogen free compliance

Specifications

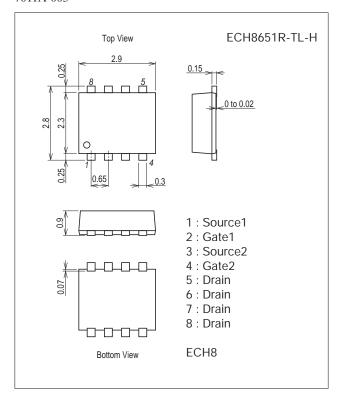
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		24	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	ID		10	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.4	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² x0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7011A-003



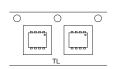
Product & Package Information

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

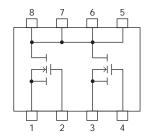
Packing Type: TL



Marking



Electrical Connection

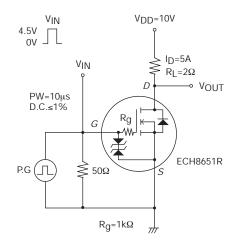


ECH8651R

Electrical Characteristics at Ta=25°C

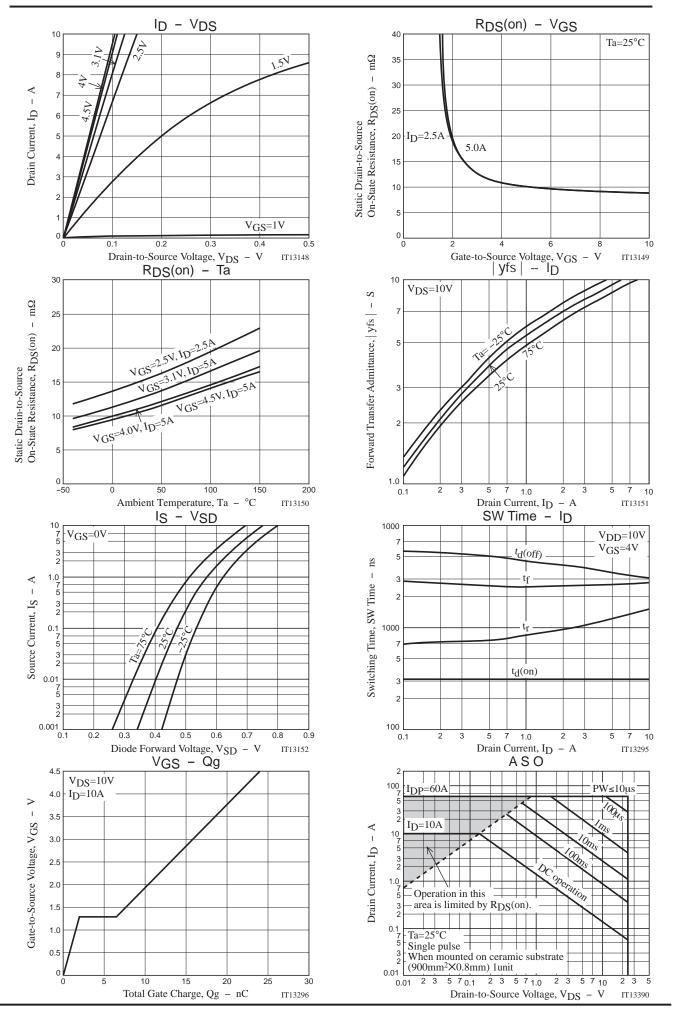
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Uniii	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	24			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.5		1.3	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =5A	5.5	9.5		S	
	R _{DS} (on)1	I _D =5A, V _G S=4.5V	7	10.5	14	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =5A, V _G S=4.0V	7.2	11	15	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)3	I _D =5A, V _G S=3.1V	7.5	12.5	17.5	mΩ	
	RDS(on)4	ID=2.5A, VGS=2.5V	9	15	21	mΩ	
Turn-ON Delay Time	t _d (on)			300		ns	
Rise Time	t _r	Con appointed Toot Circuit		1000		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		4000		ns	
Fall Time	tf			2500		ns	
Total Gate Charge	Qg			24		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =10A		2		nC	
Gate-to-Drain "Miller" Charge	Qgd			4.5		nC	
Diode Forward Voltage	V _{SD}	I _S =10A, V _{GS} =0V		0.77	1.2	V	

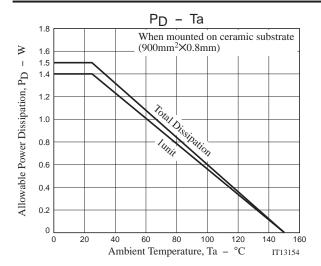
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo	
ECH8651R-TL-H	CH8651R-TL-H ECH8		Pb Free and Halogen Free	



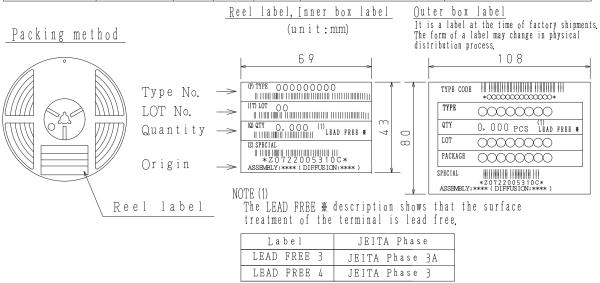


Embossed Taping Specification

ECH8651R-TL-H

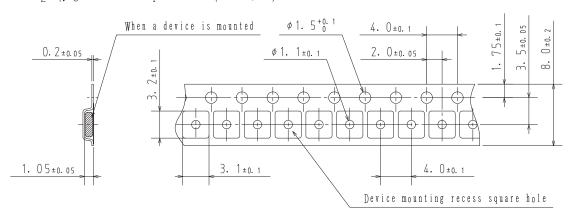
1. Packing Format

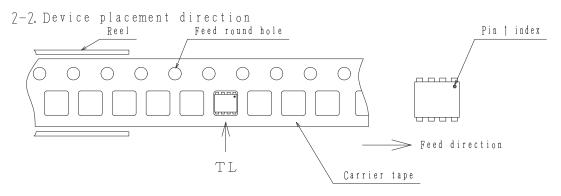
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	g format		
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)		
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained		
					Dimensions:mm (external)	Dimensions:mm (external)		
					183×72×185	440×195×210		



2. Taping configuration

2-1. Carrier tape size (unit:mm)





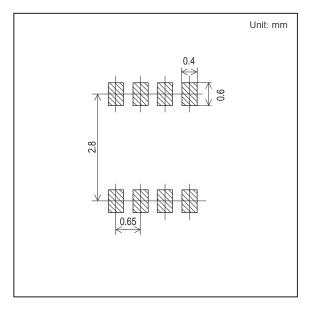
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8651R-TL-H

Mass (g) Unit 0.02 * For reference mm 0. 15^{+0. 1}_{-0. 05} 0. 25±0.06 2. 9±0.06 0~0.02 2. 8±0.05 2. 3±0.06 LOT No. 0. 25±0.06 0. 3^{+0. 1} PIN#1 0. 9±0. 05 0.05 \$ \$

Land Pattern Example



Note on usage: Since the ECH8651R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equa